

(Japanese Pat. Appln. No. 264225/1997)
(Translation)
Page 1

SPECIFICATION

Title of the Invention

SEMICONDUCTOR LAYER FORMED BY SELECTIVE DEPOSITION AND METHOD FOR DEPOSITING THE SAME, NITRIDE-BASED SEMICONDUCTOR LAYER FORMED BY SELECTIVE DEPOSITION AND METHOD FOR DEPOSITING THE SAME, NITRIDE-BASED SEMICONDUCTOR LIGHT EMITTING DEVICE AND METHOD FOR FORMING THE SAME

Claim

1. A method for depositing a semiconductor layer, wherein after a mask having an opening is formed by using a material including an element which makes a semiconductor layer into a first conductivity type, at least one semiconductor layer of a second conductivity type is selectively grown in said opening at a growth temperature which is higher than a temperature where the material of said mask is decomposed, characterized in that a portion of constituent elements of said material of said mask is the same as a portion of constituent elements of said semiconductor layer.
2. A method for depositing a nitride-based semiconductor layer, wherein after a mask having an opening is formed by using a material including an element which makes a nitride-based semiconductor layer into a first conductivity type, at least one nitride-based semiconductor layer of a second conductivity type is selectively grown in said opening at a growth temperature which is higher than a temperature where the